Stabilization of high-pressure GeCu$_2$O$_4$ spinel cuprate with quasi-1D $S = 1/2$ chains in the epitaxial thin-film form

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(Dated: September 11, 2019)

Abstract

GeCu$_2$O$_4$ is a high-pressure recoverable cuprate with a strongly tetragonally elongated spinel structure and magnetic lattice formed by $S = 1/2$ CuO$_2$ linear chains with frustrated exchange interactions and exotic magnetic behavior. Here we report on the first stabilization of epitaxial thin films of GeCu$_2$O$_4$ on (001)-oriented MgAl$_2$O$_4$ substrate. Developed growth mode, surface morphology, crystal structure and copper valence state were characterized by in-situ reflection high-energy electron diffraction, atomic force microscopy, X-ray reflectivity, X-ray diffraction and X-ray photoelectron spectroscopy. The availability of large single-crystalline GeCu$_2$O$_4$ thin films paves road to comprehensive investigation of physical properties including the puzzle of magnetism and multiferroicity in this peculiar compound.
Complex oxide materials with Cu ions embedded into their structural motif are among most studied compounds of the modern condensed matter physics. These materials often crystallize in unique structures with fascinating physical properties with the most celebrated example represented by high temperature cuprate superconductors\textsuperscript{[1]}. Many other copper oxides also possess non-trivial physical properties including exotic low-dimensional magnetism. In particular, one-dimensional (1D) spin chains can be mapped into the simplest theoretical models yet with several surprising phenomena, e.g. the Haldane conjectures\textsuperscript{[2]}, i.e the fundamental difference between integer (spin-gapped) and half-integer (spin-gapless) spin chains\textsuperscript{[3]}, and unusual ballistic spinon driven thermal transport along the chains\textsuperscript{[4]}. In addition, of a particular interest are the $S = 1/2$ compounds where one anticipates strongest quantum effects. Not surprisingly, many of such systems are Cu$^{2+}$ based compounds including Sr$_2$CuO$_3$ with a very large disparity between intrachain exchange coupling $J \sim 2200$ K and Néel temperature $T_N = 5$ K \textsuperscript{[5]}, or Cs$_2$CuCl$_4$ where frustrated interchain coupling results in exotic “triplon” bound states that readily move between chains\textsuperscript{[6]}. GeCuO$_3$ is another cuprate with $S = 1/2$ Heisenberg antiferromagnetic 1D-chain which attracted strong interest due to the discovery of the first spin-Peirls transition (i.e. spin pairing with a valence bond formation) among the inorganic compounds\textsuperscript{[7]}.

Among ternary Ge-Cu-O system GeCuO$_3$ is the only stable complex compound at ambient pressure. After that, a recoverable high-pressure phase GeCu$_2$O$_4$ (GCO) discovered by Hegenbart and co-workers\textsuperscript{[8]} with hausmannite structure type (space group $I4_1/amd$) represents the second known tertiary oxide in this system. GCO has a tetragonally distorted spinel structure in which Cu$^{2+}$ occupies only the octahedral B-site which in turn forms a pyrochlore sublattice. Due to a very large Jahn-Teller effect the local coordination of Cu$^{2+}$ ions can be described as almost square-planar with the in-plane Cu-O distance of 1.939 Å while the apical oxygens set at 2.504 Å \textsuperscript{[8]}.

As illustrated in Figure \textsuperscript{1}a this feature allows to consider this distorted spinel structure as comprised by alternating mutually perpendicular layers of 1D CuO$_2$ $S = 1/2$ chains interconnected via GeO$_4$ tetrahedra. The 1D nature of magnetic interactions within the chains are supported by magnetic susceptibility data which show the characteristic Bonner-Fisher behavior\textsuperscript{[9]} with the ratio of inter-chain to intra-chain exchange couplings $J'/J \sim 0.16$ and these data also indicate onset of the long-range magnetic ordering at 33 K \textsuperscript{[10]}.

Despite such a large tetragonal distortion of the pyrochlore sublattice the magnetic in-
FIG. 1. a) Crystal structure of GeCu$_2$O$_4$ with alternating 1D CuO$_2$ chains in perpendicular directions. b) and c) RHEED patterns of MgAl$_2$O$_4$ substrate and GeCu$_2$O$_4$ film at at 600 °C. d) 2θ − ω X-ray diffraction scan along 00l direction. The scan contains allowed reflections of the substrate and fabricated film together with two forbidden reflections (002 and 006) of the substrate which arise because of Umweganregung effect[16]. The inset shows asymmetric shape of (004) GCO peak which indicates relaxation of the substrate-induced strain.

Interaction between Cu ions in GeCu$_2$O$_4$ remain frustrated in close analogy to the above-mentioned Cs$_2$CuCl$_4$ case. Theoretically, such anisotropic pyrochlore lattice was mapped into a 2D crossed-chain model[11] which predicts the formation of a valence-bond solid with a crossed-dimer state in the limit of small $J'/J$[11]. Contrary to the model calculations, the numerical study of GCO suggests the formation of a spiral magnetic ground state[12]. The subsequent neutron powder diffraction study revealed the presence of collinear antiferromagnetism at low temperatures with an unexpected up-up-down-down (i.e. ↑↑↓↓) spin ordering pattern along the chains[13]. Such unusual ordering pattern was attributed to the importance of the biquadratic exchange interaction in this compound[13]. To add to the further surprises, two independent groups recently reported spin-induced multiferroicity emerging at $T_N \sim 33$ K [14 and 15], the result which is incompatible with any theory proposed or experimentally determined magnetic structures[11-13]; to date the nature of multiferroicity in GCO remains unknown.

One of the key obstacles which impends the experimental investigation of GCO is the absence of large single crystals. As this spinel phase is only stable at high-pressure ($\sim 4$ GPa[8])
its synthesis requires high-pressure equipment that yields only micron-sized single crystals. Availability of high-quality thin films of GCO can help to overcome this problem as epitaxial strain can stabilize phases which otherwise are unstable at ambient pressure in the bulk form.

In this letter we report on the first fabrication of (001)-oriented GCO films on MgAl$_2$O$_4$ (MAO) (001)-oriented substrate using the pulsed laser deposition. The developed growth mode, surface morphology, film thickness and crystal structure were characterized by *in-situ* reflection high-energy electron diffraction (RHEED), atomic force microscopy (AFM), X-ray reflectivity (XRR) and X-ray diffraction (XRD). Valence state of copper and stoichiometry of the film surface were studied by X-ray photoelectron spectroscopy (XPS). The combination of advanced tools confirms the successful epitaxial growth of (001)-oriented GCO thin films of large 5 × 5 mm$^2$ area.

First, we start with the description of our thin film synthesis efforts. Since the bulk GeCu$_2$O$_4$ is the high-pressure phase, it is natural to deposit film on the substrate with compressive strain. Due to the very large tetragonal elongation along $c$-axis, GCO lattice is strongly compressed in the $ab$ plane resulting in no suitable substrate crystal with spinel structure to provide compressive strain in the $ab$ plane.$^{[17]}$ As a compromise, we selected two substrates for our experiments: (i) (001)-oriented SrTiO$_3$ (STO) with perovskite structure which would result in compressive strain for the epitaxial growth of GCO and (ii) (001)-oriented MgAl$_2$O$_4$ (MAO) spinel substrate which is isostructural to GCO but provides moderate tensile strain.

In the series of depositions on (001)-oriented STO we varied both substrate temperature (controlled by pyrometer) from 470 to 700 °C and background oxygen pressure from 5 to 100 mTorr. The GCO phase was not stabilized in any of these growth experiments.

Next, we developed a series of depositions on (001)-oriented MAO substrate. At low oxygen pressure of ∼ 5 mTorr and in the temperature range 600 – 700 °C all the samples show the appearance of Cu$_2$O phase with Cu ions in +1 oxidation state; a same result as for STO substrate at these conditions. However, upon increasing of oxygen pressure the GeCu$_2$O$_4$ phase was stabilized in the range of 600 – 700 °C and at pressures > 50 mTorr.

Further growth work confirmed that the best quality GCO films grow at 50 mTorr of O$_2$ and 600 °C substrate temperature. The UV-laser was operated at 3 Hz repetition rate with 3.1 J/cm$^2$ energy density per pulse. After deposition all samples were annealed at the
FIG. 2. High resolution XPS scans of a) Ge 2p shell, b) Cu 2p shell and c) O 1s shell. The copper scan shows mostly Cu$^{2+}$ (light-blue lines) with developed satellite features. The minor amount of Cu$^{1+}$ and different state of O (green lines) is likely related to the surface decomposition of the film.

growth condition and then gradually cooled down (15 °C/min) to room temperature at the same oxygen pressure.

During synthesis, growth was monitored by in-situ high-pressure RHEED. The representative RHEED pattern of the 26 nm thick (determined from XRR curve) GCO film is shown in Fig. 1c. The intensity of the specular reflection shows only an initial reduction at the start of the deposition followed by intensity recovery. As the growth sequence progressed, it remain largely constant and without any evident oscillations. The elongated RHEED streaks with intensity modulation in Fig. 1c indicate the presence of a multilevel stepped surface [18]. Our AFM scans corroborate the presence of the flat terraces with low area roughness $S_a \sim 100 - 200$ pm, which is very similar to the quality of the MAO substrate surface. The XRR measurement yields 240 pm average surface roughness which is in a good agreement with the AFM scans. Furthermore, the RHEED pattern of the 50 nm thick film (determined from the number of laser pulses) shows clear signs of 3D surface islands. This observation is consistent with the absence of oscillations in the XRR spectrum. Overall, these observations imply that GCO films grow in a step-flow mode which turns into 3D island mode at the beginning of epitaxial strain relaxation (more details are given below).

Next we discuss results of the diffraction experiments which were done using Cu $K_\alpha$ radiation. The 00$l$ scan of the 50 nm thick GCO film shown in Fig. 1d contains two reflections of the GCO film apart from the substrate reflections. These peaks can be indexed as 004 and 008 reflections confirming (001)-orientation and epitaxial growth of the film.

To determine in-plane strain for the GCO sample we recalculate lattice parameters of the
MAO unit cell from the face-centered to the equivalent body-centered lattice \((a_I = a_F/\sqrt{2})\). The bulk GCO lattice parameters are \(a = 5.593\ \text{Å} \) and \(c = 9.395\ \text{Å}\) and growth on the MAO substrate \((a_F = 8.08\ \text{Å})\), therefore, should result in 2.15% in-plane tensile strain. Indeed, our diffraction data for the 25 and 50 nm thick films yield the 9.31 and 9.37 Å out-of-plane lattice constant that is consistent with tensile strain. This difference in the lattice constant for 25 and 50 nm thick films implies a different degree of partial relaxation of epitaxial strain. The partial relaxation can be clearly seen from the asymmetric shape of (004) GCO peak in the inset of Fig. 1d.

To verify Cu oxidation state and stoichiometry of the film surface we collected XPS spectra (see Fig. 2) on Thermo Scientific K-Alpha XPS spectrometer with monochromated Al \(K\alpha\) radiation. As seen, the scan around Cu 2\(p\) core state shows that a majority of copper ions have the expected 2+ oxidation state (935 eV 2\(p_{3/2}\) peak) with the well-developed satellite features shown in Fig. 2b. A small feature seen at 933.5 eV (\(\sim 9\%\) of total Cu signal) implies the surface contamination with Cu\(^{1+}\). This observation is consistent with the fact that our high-resolution scans around 2\(p\) state of Ge and Cu yield Ge : Cu \(\approx 1 : 1.2\) which is also in variance with the bulk-like GeCu\(_2\)O\(_4\) composition. On the other hand, the XRD data do not show the presence of any additional phases which is in agreement with the absence of granulation in AFM scans common for multiphase films. Based on these observations, the samples are single-phase films and we attribute the small admixture of Cu\(^{1+}\) and deviation in the cation ratio to the problems with termination layer and/or degradation of the air-exposed surface of GCO films.

To further corroborate that the film is indeed the target GeCu\(_2\)O\(_4\) phase we carried out a reciprocal space mapping (RSM) of the 50 nm film. Here we note that since the out-of-plane lattice parameter of the film significantly differs from the substrate (9.37 Å vs 8.08 Å) the positions of the substrate and film peaks diverge considerably. The relevant part of reciprocal space is plotted in Fig. 3. Because of geometrical limitations in our diffractometer the first available asymmetric reflection is the (206) substrate peak but the equivalent (116) film peak almost lies on the substrate \(h05\) line. As the result, one cannot perform a usual RSM single scan which include both substrate and film peaks as such scan would be impractically long. Instead, we measured two separate scans around the MAO (206) peak and expected position of GCO (116) peak.

Indeed, the film peak was found in the predicted position (see Fig. 3) that in turn confirma
FIG. 3. Reciprocal space mapping of the GCO film. On the left the reciprocal lattices of MAO substrate together with GCO film are drawn for the case of (001) epitaxial growth. The orientation of the scans coincide with drawn reciprocal lattice i.e. $Q_x$ and $Q_y$ are parallel to $h00$ and $00l$ directions of the substrate reciprocal lattice, respectively. The top-right figure is a scan around the 206 substrate reflection. The vertical stripe is due to non-monochromaticity of laboratory Cu $K_\alpha$ source. The inset shows zoomed 206 peak where one can see both $K_{\alpha 1}$ and $K_{\alpha 2}$ doublet peaks. The bottom-right figure is a scan around the 116 film reflection. The vertical red line designates the $Q_x$ coordinate of the substrate peak.

stabilization of the desired GCO phase. The $Q_x$ of 0.1945(5) rlu is larger than respective value of the (206) substrate peak (see Fig. 3) yielding 5.62 Å for the in-plane film lattice parameter, which again corroborates above-mentioned conclusion about partial relaxation of the tensile strain.
In summary, for the first time we have grown single crystalline epitaxial thin-films of high-pressure GeCu$_2$O$_4$ with the $S = 1/2$ linear chains. Detailed diffraction experiments and XPS measurements confirmed the stabilization of this peculiar phase at ambient pressure. Upon air exposure GCO shows chemical instability resulting in a small fraction of Cu$^{1+}$. The large area GeCu$_2$O$_4$ thin films will open road towards detailed experimentation to reveal nature of ground state magnetism and elucidate origin of multiferroicity in this compound.

This work was supported by the Gordon and Betty Moore Foundation’s EPiQS Initiative through Grant No. GBMF4534, and by the Department of Energy under Grant No. de-sc0012375.

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